

STRUCTURE AND METHOD OF FORMING BITLINE
CONTACTS FOR A VERTICAL DRAM ARRAY USING A
LINE BITLINE CONTACT MASK

ABSTRACT OF THE DISCLOSURE

5 A bitline contact and method of forming bitline
contact for a vertical DRAM array using a bitline
contact mask. In the method, gate conductor lines
are formed. An oxide layer is deposited over the
gate conductor lines, and a bitline contact mask is
10 formed over portions of the oxide layer. The
bitline contact mask is etched, and a silicon layer
is deposited on the substrate. A bitline layer is
deposited on the silicon layer. A masking and
etching operation is performed on the bitline layer.
15 A M0 metal is deposited over the silicon layer and
on sides of non etched portions of the bitline (M0)
layer to form left and right bitlines.